l Number 1		Search Text -438/14:.CCLS.	DB USPAT; US-PGPUB;	Time stamp 2003/01/03 13:44
-	2	("5940704").PN.	EFD; JFD; CERWENT; IBM_TDB USPAT; US-FGPUB;	2002/12/31 14:14
-	3	5940704.URPN.	EPT; JED; DEPWENT; JEM_TDE DOSĀT	.001/12/31 13:04
-	1921	second and transistor and reference adj voltage and measuring and testing	USFAT; USFEGEUB; EFL; TEU; DEFWENT; IBM TIE	2001/12/31 13:06
-	37	measuring adj current near drain	USPĀT; US-PGPUB; EFD; JPO; DEFWENT;	0001/11/31 13:29
-	0	reticle adj option adj layer	IBM_TOB USPAT; US-PGTUB; EFD; IFD; DEFWENT;	.001/10/31 13:13
-	37196	wafer and test	IEM_TOE USPAT; US-PGFUE; EFD; JPC; DEPWENT;	2002/12/31 13:32
-	17233	reticle	IBM_TOB USPAT; US-PGHOF; EEP; UPO; HERWENT;	2002/12-31 13:15
-	1638	(wafer and test) and reticle	IPM_TUB USEAT; USEPSEUB; EEG; UPI; LEFWENT;	2001/10 31 13:16
-	13608		IEM_FIB USFAT; US-PGFUE; EFF; JPU; LERWENT;	2001/11 31 13:16
-	123	((wafer and test) and reticle) and ((probe or probing) and die)	IBM TLB USPAT; US-PGFUB; EFO; CPD; DEFWENT;	2002/12/31 13:17
-	990341	pin	IBM TIB USEAT; US-PGEUB; EFL; UED; DEFWENT;	2002/12/31 13:17
-	5333	test adj voltage	IBM TDE USPAT; US-PGPUR; EPU; JPU; DEFWENT;	2002/12/31 14:20
-	0	((wafer and test) and reticle) and ((brobe or probing) and die)) and pin) and (test adj voltage)	IBH <u>TDB</u> USHAT;	2002/12/31 13:16

- 57	() wafer and test; and reticle, and ((probe or probing, and die); and pin	USPAT; US-PGPUB; EFD; UFD; DERWENT;	2002/1:/31 13:28
- 7514	"burn-in"	IRM_TOP USPAT; US-PGPUB; EFO; IFO; DESWENT;	2007/11/31 13:28
- 1997	(wafer and test) and "burn-in"	IEM_TOE USFAT; US-EGPUB; EFU; UFD;	3001/11/31 14:33
- 695	((probe or probing) and die) and ((wafer and test) and "burn-in":	CEPWENT; IBM_FOB USFAT; US-FGBUB; EFD; IFL; LEFWENT;	2002/12/31 13:28
- 462	<pre>pin and (((probe or probing) and die) and ((wafer and test) and "burn-in"))</pre>	IBM TEB	2002/12/31 13:28
- 11376	measuring adj current	IEM_TOB USPAT; US-PGFUB; EPO; IPO; DEFWENT;	2001/12/31 13:29
- 8	<pre>(pin and (((probe or probing) and die) and ((wafer and test) and "burn-in"))) and (measuring adj current)</pre>	IBM_TOB USFAT; US-PGFUE; EPC; UPC;	2001/12 31 13:31
- 133141	reference adj voltage	DERWENT; IBM_TOB USFAT; US-PGFUB; EP1; JP2;	0001 10 31 13:32
- 152	(wafer and test) and "burn-in" and (reference adj voltage)	DEFWENT; IBM_TEB USFAT; US-PGFUB; EPO; UPO; DEPWENT;	1000/12/31 13:32
- 153889	source and gate and drain	IBM_TLB USFAT; US-PGFUB; EPO; JPO; LEPWENT;	1002 12/31 13:33
- 88	((wafer and test) and "burn-in" and (reference adj voltage)) and (source and gate and drain)	IBM_TDB USFAT; US-PGPUB; EPT; JPO; DEFWENT;	1002/12 31 13:47
- ć	<pre>(measuring adj current) and (((wafer and test) and "burn-in" and reference adj voltage)) and (source and gate and drain))</pre>	IBM_TIB USFAT; US-PGFUF; EP1; JPG; DEFWENT;	1002 12 31 13:47
- 2	("4758863").PN.	IBM TDB USFAT; US-PGFUB; EPC: JPO; DEFWENT;	2002 12 31 14:14
	4088843.URPN.	IBM_TEB USPAT	2002,12,31 14:14

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27 (wafer and test) and "burn-in" and (process adj control:

USFAT; 2002/12/31 14:22 US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB USFAT; 2002/12/31 14:23 US-PGPUB; EPG; JPO; DERWENT; IBM_TDB